

IRRLI540N-VB Datasheet

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.034 at $V_{GS} = 10$ V	50 ^a

FEATURES

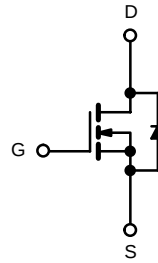
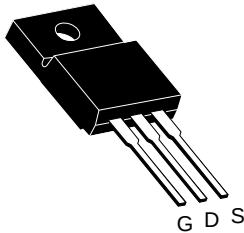
- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_g Tested


RoHS
 COMPLIANT

APPLICATIONS

- Isolated DC/DC Converters

TO-220 FULLPAK



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	50 ^a	A
		28 ^a	
Pulsed Drain Current	I_{DM}	120	
Avalanche Current	I_{AS}	31	
Single Pulse Avalanche Energy ^b	E_{AS}	61	mJ
Maximum Power Dissipation ^b	P_D	360 ^c	W
		3.70	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes:

- Package limited.
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	100			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5		2.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.034		Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C		0.063		
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C		0.084		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	25			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5100		pF
Output Capacitance	C _{oss}			480		
Reverse Transfer Capacitance	C _{rss}			210		
Total Gate Charge ^c	Q _g	V _{DS} = 100 V, V _{GS} = 10 V, I _D = 65 A		90	130	nC
Gate-Source Charge ^c	Q _{gs}			23		
Gate-Drain Charge ^c	Q _{gd}			34		
Gate Resistance	R _g		0.5	1.7	3.3	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 100 V, R _L = 1.5 Ω I _D ≅ 65 A, V _{GEN} = 10 V, R _g = 2.5 Ω		24	35	ns
Rise Time ^c	t _r			220	330	
Turn-Off Delay Time ^c	t _{d(off)}			45	70	
Fall Time ^c	t _f			200	300	
Source-Drain Diode Ratings and Characteristics T _C = 25 °C ^b						
Continuous Current	I _S			50		A
Pulsed Current	I _{SM}			120		
Forward Voltage ^a	V _{SD}	I _F = 65 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		130	200	ns
Peak Reverse Recovery Current	I _{RM(REC)}			8	12	A
Reverse Recovery Charge	Q _{rr}				0.52	1.2

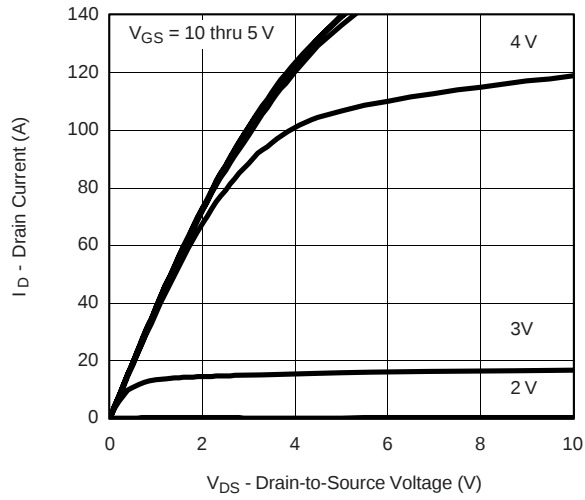
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

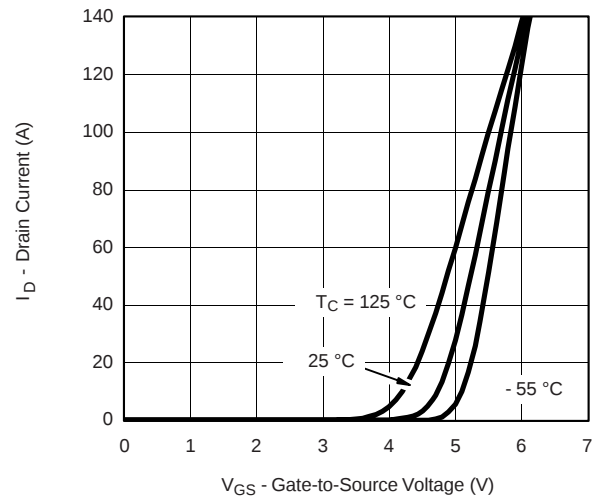
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

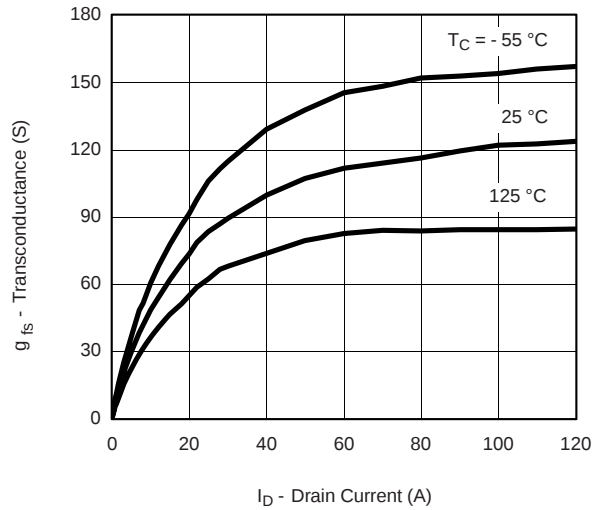
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



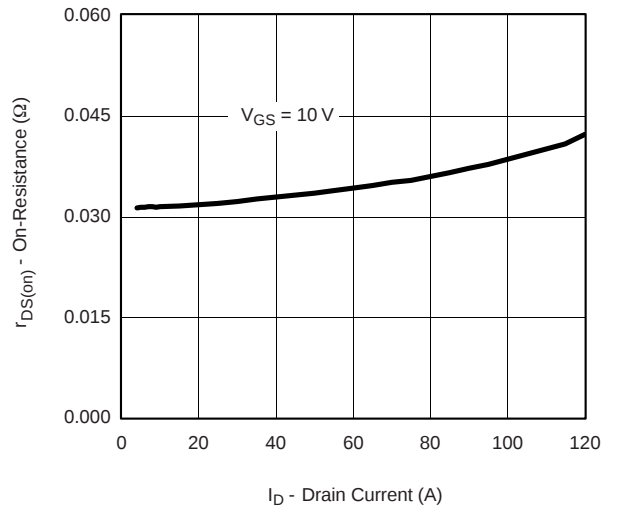
Output Characteristics



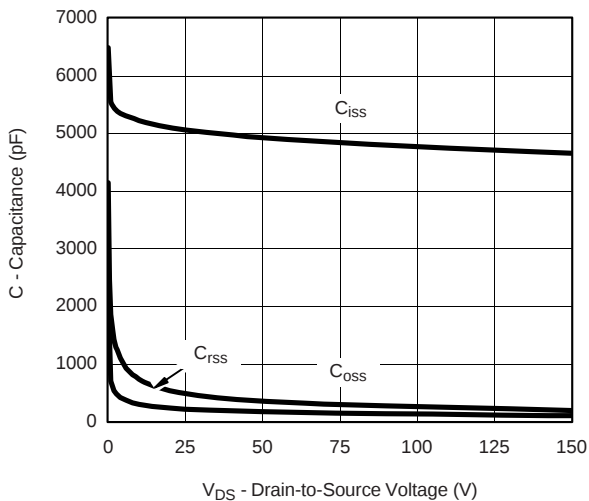
Transfer Characteristics



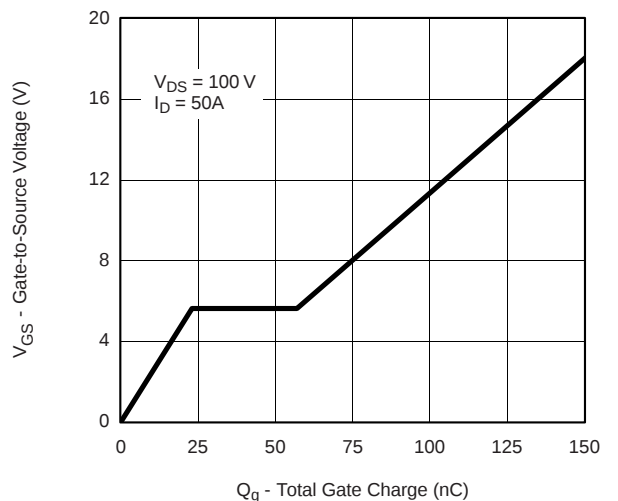
Transconductance



On-Resistance vs. Drain Current

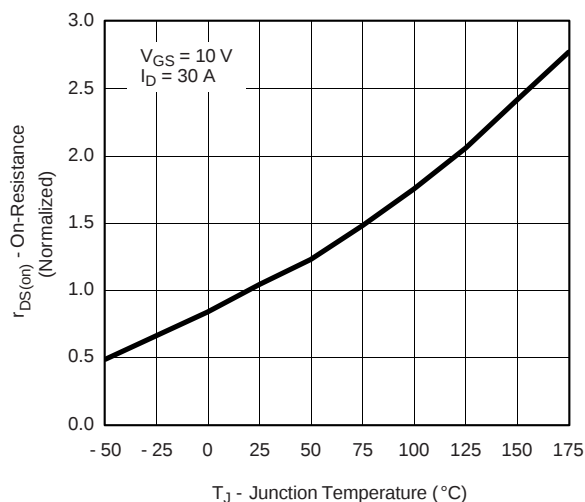


Capacitance

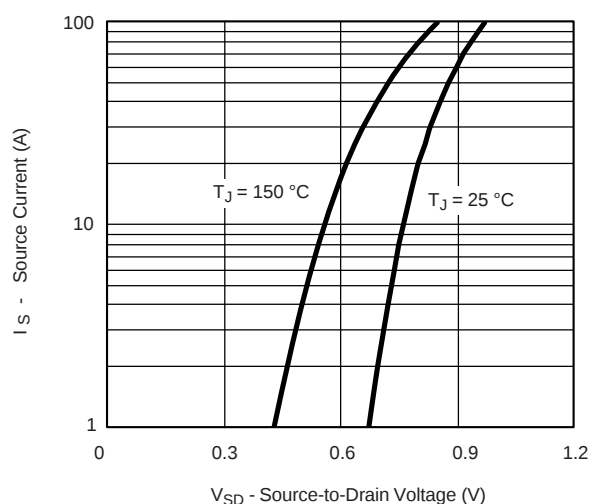


Gate Charge

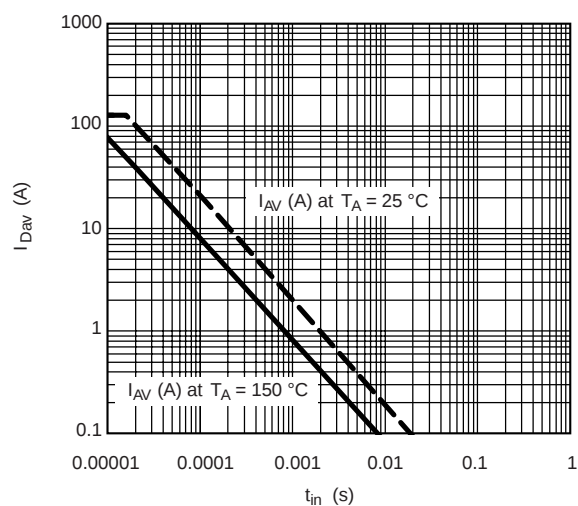
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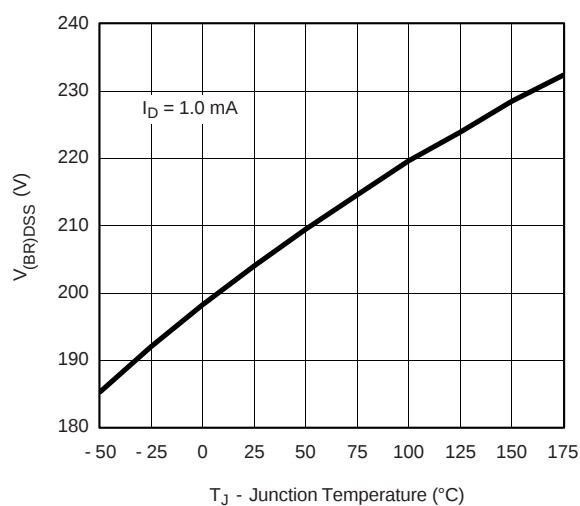
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

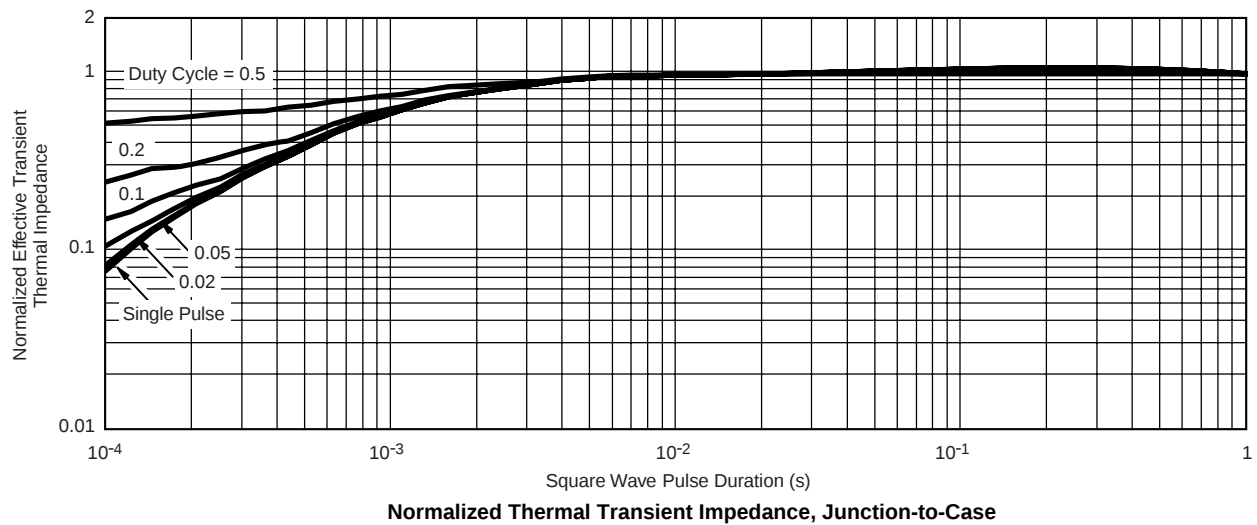
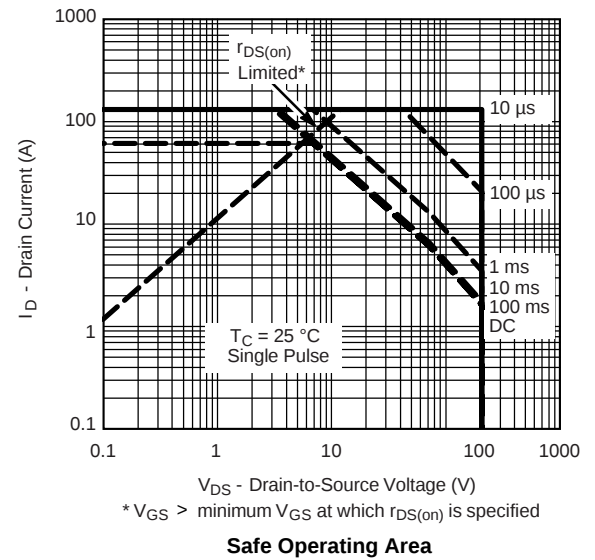
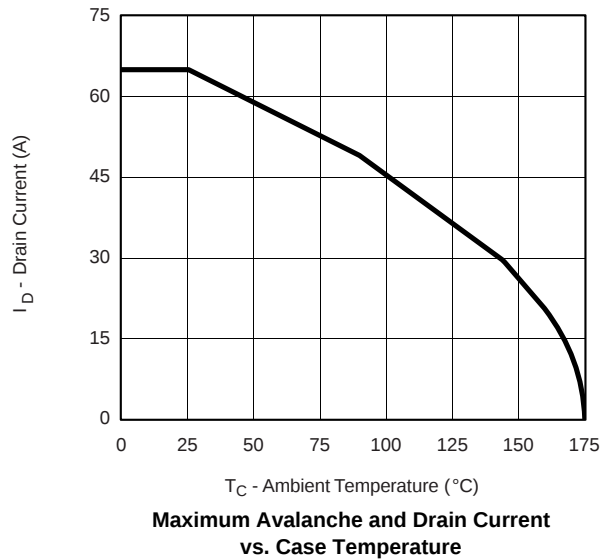


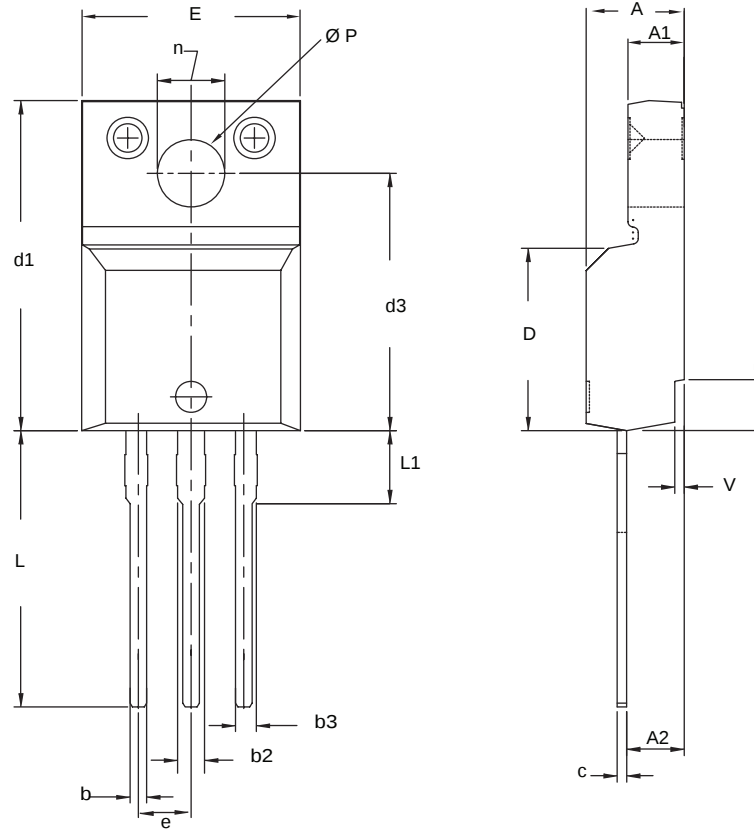
Avalanche Current vs. Time



Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS



TO-220 FULLPAK (HIGH VOLTAGE)

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
 DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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